

# Abstracts

## Analysis of the Source Inductance Effect on the Power Performance of High Development HEMT's in the Ka-Band

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*C. Gaquiere, B. Bonte, D. Theron, Y. Crosnier and J. Favre. "Analysis of the Source Inductance Effect on the Power Performance of High Development HEMT's in the Ka-Band." 1995 Microwave and Guided Wave Letters 5.8 (Aug. 1995 [MGWL]): 243-245.*

This paper provides an analysis of the power performance degradations of interdigitated HEMT's in millimeter wave range as the total gate width increases. It investigates the possibility of optimizing the device topologie by combining a limited number of via holes and airbridge source connections in order to offer a good cost-performance trade-off.

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